

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 02-172895
(43)Date of publication of application : 04.07.1990

(51)Int.CI. C30B 29/36
C30B 25/14
H01L 21/205

(21)Application number : 63-325220 (71)Applicant : NEC CORP
(22)Date of filing : 22.12.1988 (72)Inventor : OSHITA YOSHIO

(54) METHOD FOR GROWING SEMICONDUCTOR CRYSTAL

(57)Abstract:

PURPOSE: To uniformly grow an SiC crystal film having a thickness controlled on the order of an atomic layer by CVD on the entire surface of a substrate having a large area by alternately introducing a mixture of gaseous hydrogen chloride with gaseous silicon chloride and gaseous hydrocarbon into a growth system.

CONSTITUTION: When an SiC crystal is grown by CVD with gaseous silicon chloride and gaseous hydrocarbon as starting materials, a mixture of gaseous hydrogen chloride with gaseous silicon chloride such as SiH₂Cl₂ and gaseous hydrocarbon such as C₂H₂ are alternately introduced into a growth system and an SiC crystal film is grown. Gaseous carbon chloride may be introduced in place of the gaseous hydrocarbon.

LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]